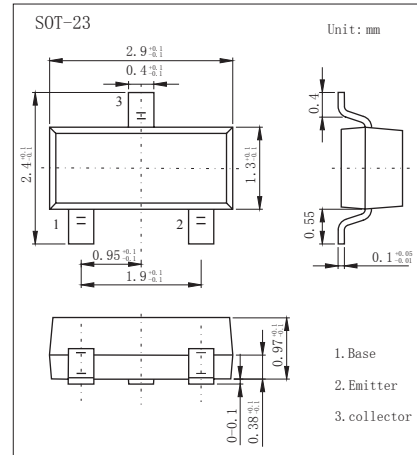


PNP Transistors

BCW68

■ Features

- Complementary to BCW66, BCW68 is subdivided into three groups F, G and H according to its DC current gain.



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-60	V
Collector - Emitter Voltage	V_{CE0}	-45	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_c	-800	mA
Collector Power Dissipation	P_c	330	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	



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PNP Transistors

BCW68

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = -100 μA, I _E =0	-60			V
Collector- emitter breakdown voltage	V _{CE0}	I _c = -10 mA, I _B =0	-45			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 μA, I _c =0	-5			
Collector-base cut-off current	I _{CB0}	V _{CB} = -45 V, I _E =0			-20	nA
Emitter cut-off current	I _{EB0}	V _{EB} = -4V, I _c =0			-20	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =-100 mA, I _B =-10mA			-0.3	V
		I _c =-500 mA, I _B =-50mA			-0.7	
Base - emitter saturation voltage	V _{BE(sat)}	I _c =-100 mA, I _B =-10mA			-1.25	
		I _c =-500 mA, I _B =-50mA			-2	
DC current gain	h _{FE(1)}	V _{CE} = -10V, I _c = -0.1mA	F	35		
			G	50		
			H	80		
	h _{FE(2)}	V _{CE} = -1V, I _c = -10mA	F	75		
			G	120		
			H	180		
	h _{FE(3)}	V _{CE} = -1V, I _c = -100mA	F	100		250
			G	160		400
			H	250		630
	h _{FE(4)}	V _{CE} = -2V, I _c = -500mA	F	35		
			G	60		
			H	100		
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f=1MHz		6		pF
Collector input capacitance	C _{ib}	V _{EB} = -0.5V, I _E = 0, f=1MHz		60		
Transition frequency	f _t	V _{CE} = -5V, I _c = -50mA, f=20MHz		200		MHz

■ Classification of h_{FE(3)}

Type	BCW68F	BCW68G	BCW68H
Range	100-250	160-400	250-630
Marking	DF	DG	DH



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SMD Type Transistors

PNP Transistors

BCW68

Typical Characteristics

